

# NX3020NAK

# **30 V, single N-channel Trench MOSFET**

29 October 2013

**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	200	mA
Static charact	teristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{j}$ = 25 °C		-	2.7	4.5	Ω

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.





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## 5. Pinning information

**Table 2.** Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1	G S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX3020NAK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX3020NAK	%CU

<sup>[1] % =</sup> placeholder for manufacturing site code

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	200	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	125	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	800	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	300	mW
			[1]	-	360	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>sp</sub> = 25 °C		-	1060	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	'	,			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

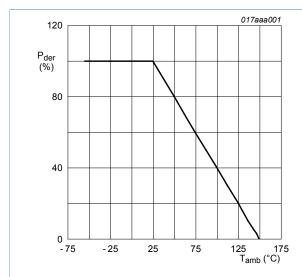


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\%)}} \times 100\%$$

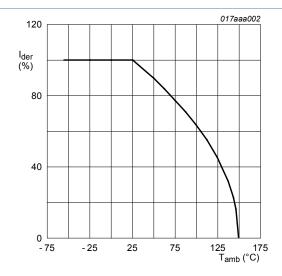
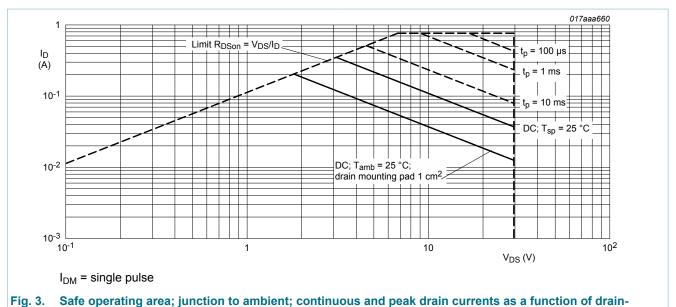


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{DQ5^{\circ}C}} \times 100 \%$$

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# source voltage

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from j	thermal resistance	om junction to	[1]	-	350	400	K/W
	from junction to ambient		[2]	-	300	340	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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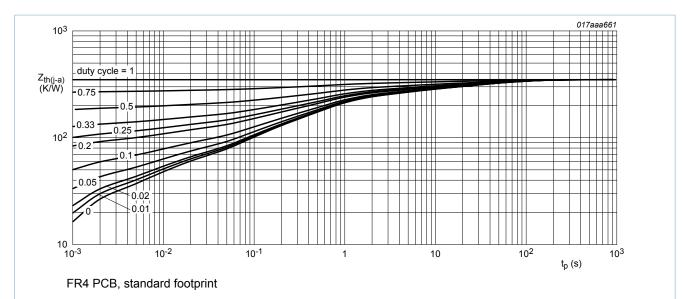


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

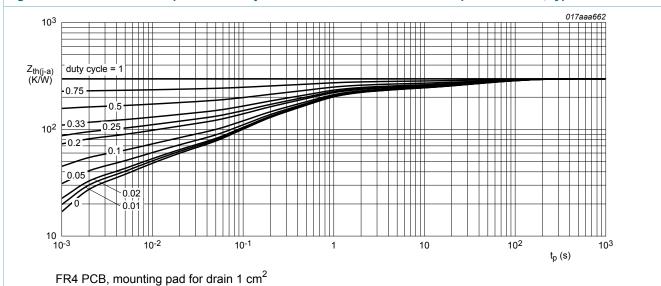


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \text{ A}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	8.0	1.2	1.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μΑ
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3.5	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-3.5	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.5	μA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{j}$ = 25 °C	-	2.7	4.5	Ω
		$V_{GS}$ = 10 V; $I_{D}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{j}$ = 150 °C	-	5.5	9.2	Ω
		$V_{GS}$ = 4.5 V; $I_{D}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{j}$ = 25 °C	-	3	5.2	Ω
		$V_{GS}$ = 2.5 V; $I_{D}$ = 10 mA; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{j}$ = 25 °C	-	4	13	Ω
9fs	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 150 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{j}$ = 25 °C	320	-	-	mS
Dynamic c	haracteristics	1	l			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 150 mA; $V_{GS}$ = 4.5 V;	-	0.34	0.44	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.11	-	nC
$Q_{GD}$	gate-drain charge		-	0.06	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	13	20	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	2.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.1	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;	-	5	10	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	34	68	ns
t <sub>f</sub>	fall time		-	17	-	ns
Source-dra	in diode	1	l l	1	1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.7	1.2	V

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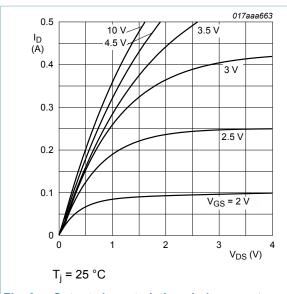


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

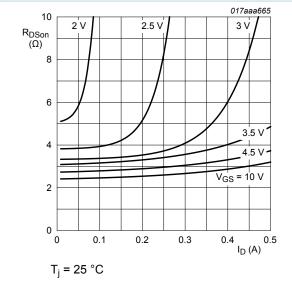


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

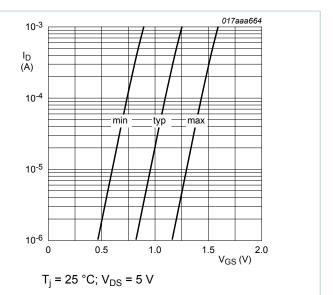


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

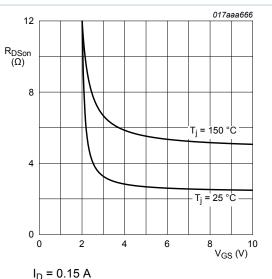


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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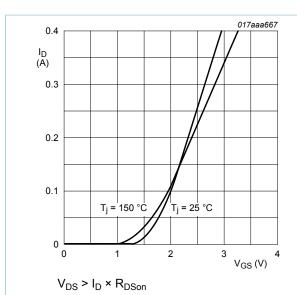


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

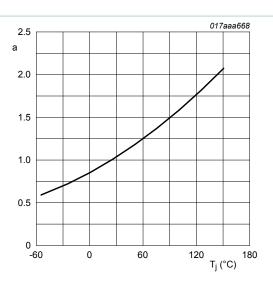


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

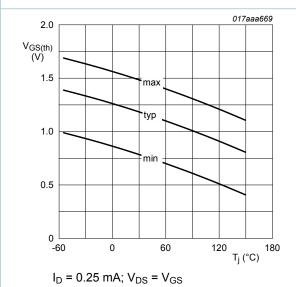
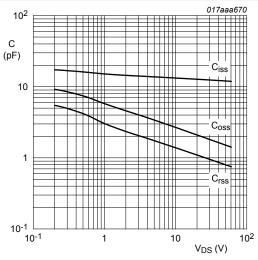


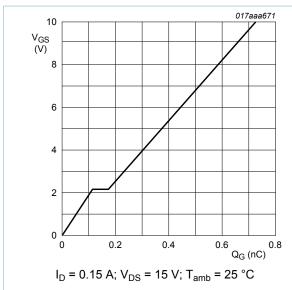
Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)
V<sub>GS</sub>(th)
V<sub>GS</sub>
Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>GG</sub>(tot)

017aaa137

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

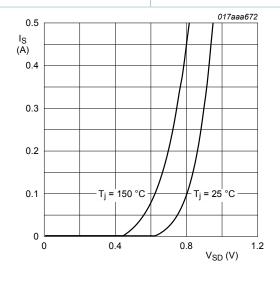
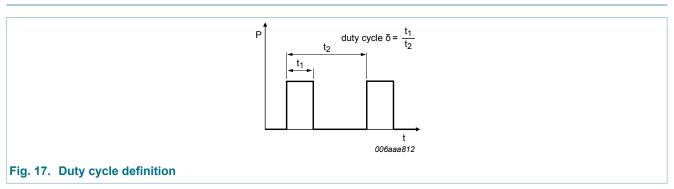


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 

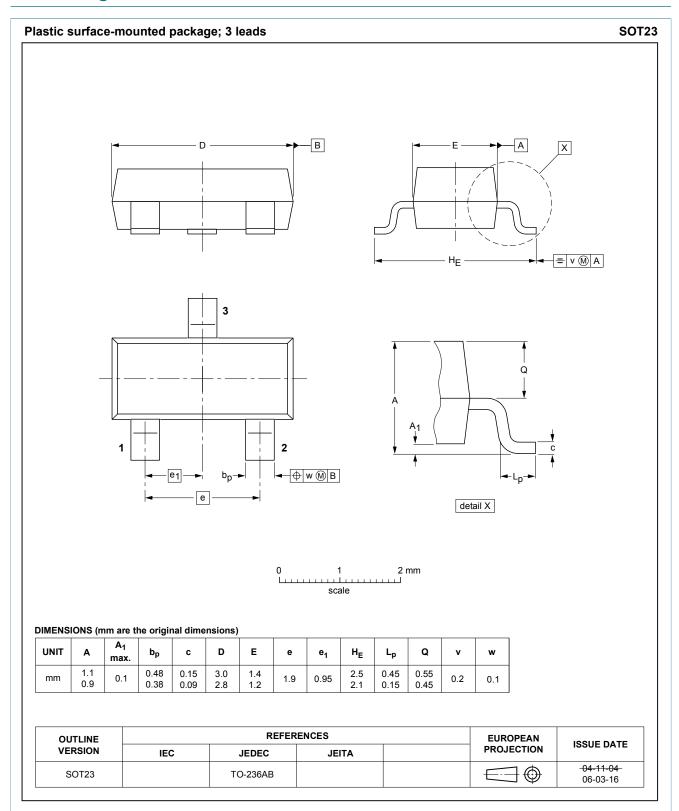


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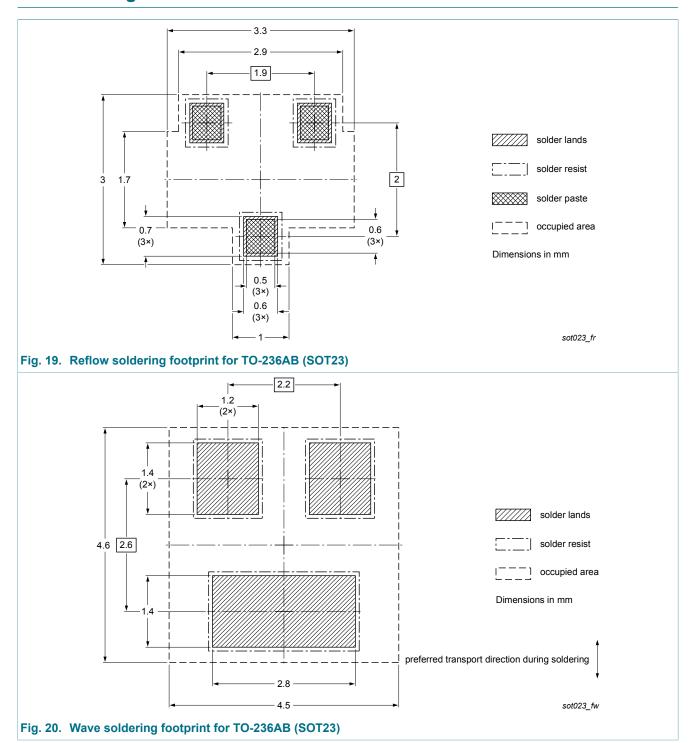
## 12. Package outline



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## 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
NX3020NAK v.2	20131029	Product data sheet	-	NX3020NAK v.1		
Modifications:	<ul> <li>and package outline added</li> <li>Table 7 values of capacitance parameters corrected</li> <li>Figure 13 corrected</li> </ul>					
NX3020NAK v.1	20121002	Product data sheet	-	-		

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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